GEMaC
Groupe d'Étude
de la Matière Condensée

MOCVD OF II-VI SEMICONDUCTORS

GEMaC has two MOCVD (Metal Organic Chemical Vapor Deposition) growth systems devoted to the growth of structures based II/VI semiconductors.

Horizontal reactor (SAT)

Main characteristics of the system:
Sources :
- Elements II: Zn, Mg, Cd
- Eléments VI: N2O, O2, t-butanol
- Doping: Al, Ga, Sb, NH3

Carrier gas: He, H2, Ar, N2
Pression : 30 torr atmospheric pressure
Temperature : induction heating 1000°C

Substrate size: up to 2×2"



Vertical reactor

Main characteristics of the system:
Sources:

- Elements II: Zn, Mg
- Elements VI: N2O, t-butanol, Se, Te, S
- Doping: Al, Ga

Carrier gas: He, H2, Ar, N2
Pressure: atmospheric
Temperature : heatinge RF 1000°C
Subastrate size 1 to 2 cm2

